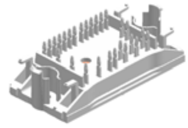
flowPIM0+PFC 2nd **600V/6A**

Features

- Clip in PCB mounting
- Trench Fieldstop IGBT's for low saturation losses
- Latest generation superjunction MOSFET for PFC

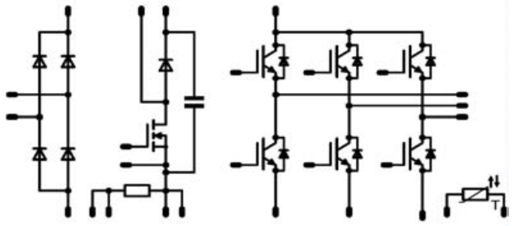
flowPIM0+PFC 2nd



Target Applications

- Industrial Drives
- Embedded Drives

Schematic



Types

- 10-F006PPA006SB-M682B

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Input Rectifier Diode					
Repetitive peak reverse voltage	V_{RRM}			1600	V
DC forward current	I_{FAV}	$T_j=T_j$max	T_h=80℃ T_c=80℃	26 36	A
Surge forward current	I_{FSM}	t_p=10ms	T_j=150℃	200	A
I2t-value	I^2t			200	A^2s
Power dissipation per Diode	P_{tot}	$T_j=T_j$max	T_h=80℃ T_c=80℃	32 48	W
Maximum Junction Temperature	$T_j$max			150	℃

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
PFC MOSFET					
Drain to source breakdown voltage	V_{DS}			600	V
DC drain current	I_D	$T_j=T_j$max	T_h=80℃ T_c=80℃	10 11	A
Pulsed drain current	I_{Dpulse}	t_p limited by $T_j$max		59	A
Avalanche energy, single pulse	E_{AS}	I_D=3,4A V_{DD}=50V	Tj=25℃	418	mJ
Avalanche energy, repetitive	E_{AR}	I_D=3,4A V_{DD}=50V	Tj=25℃	0.63	mJ
Avalanche current, repetitive	I_{AR}		Tj=25℃	3,4	A
MOSFET dv/dt ruggedness	dv/dt			50	V/ns
Power dissipation	P_{tot}	$T_j=T_j$max	T_h=80℃ T_c=80℃	47 70	W
Gate-source peak voltage	V_{GS}			20	V
Reverse diode dv/dt	dv/dt			15	V/ns
Maximum Junction Temperature	$T_j$max			150	℃
PFC Diode					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25℃		600	V
DC forward current	I_F	$T_j=T_j$max	T_h=80℃ T_c=80℃	12 12	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		18	A
Power dissipation	P_{tot}	$T_j=T_j$max	T_h=80℃ T_c=80℃	32 49	W
Maximum Junction Temperature	$T_j$max			175	℃
PFC Shunt					
DC forward current	I_F		T_c=25℃	10	A
Power dissipation per Shunt	P_{tot}		T_c=25℃	5	W

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Transistor					
Collector-emitter break down voltage	V_{CE}			600	V
DC collector current	I_C	T_j=$T_j$max	T_h=80℃ T_c=80℃	9 13	A
Pulsed collector current	I_{Cpulse}	t_p limited by $T_j$max		18	A
Turn off safe operating area		VCE ≤ 400V, Tj ≤ Top max		18	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	28 43	W
Gate-emitter peak voltage	V_{GE}			20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150℃ V_{GE}=15V		6 360	µs V
Maximum Junction Temperature	$T_j$max			175	℃
Inverter Diode					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25℃		600	V
DC forward current	I_F	T_j=$T_j$max	T_h=80℃ T_c=80℃	13 16	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		12	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80℃ T_c=80℃	21 32	W
Maximum Junction Temperature	$T_j$max			175	℃

Maximum Ratings

T_j=25℃, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
DC link Capacitor					
Max.DC voltage	V_{MAX}		T_c=25℃	500	V
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	℃
Operation temperature under switching condition	T_{op}			-40…+(Tjmax - 25)	℃
Insulation Properties					
Insulation voltage	V_{is}	t=2s	DC voltage	4000	V
Creepage distance				min 12,7	mm
Clearance				min 12,7	mm
Comparative tracking index	CTI			>200	

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Input Rectifier Diode										
Forward voltage	V_F				25	Tj=25℃ Tj=125℃		1,20 1,17		V
Threshold voltage (for power loss calc. only)	V_{to}				25	Tj=25℃ Tj=125℃		0,92 0,81		V
Slope resistance (for power loss calc. only)	r_t				25	Tj=25℃ Tj=125℃		10,9 14,4		mΩ
Reverse current	I_r			1600		Tj=25℃ Tj=125℃			0.05	mA
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2,20		K/W
PFC MOSFET										
Static drain to source ON resistance	$R_{DS(on)}$		10		6	Tj=25℃ Tj=125℃		203 398		mΩ
Gate threshold voltage	$V_{(GS)th}$	$V_{GS}=V_{DS}$			0,00063	Tj=25℃ Tj=125℃	2,4	3,0	3,6	V
Gate to Source Leakage Current	I_{GSS}		20	0		Tj=25℃ Tj=125℃			100	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	600		Tj=25℃ Tj=125℃			1000	nA
Turn On Delay Time	$t_{d(ON)}$	Rgoff=4 Ω Rgon=4 Ω	10	400	6	Tj=25℃ Tj=125℃		17 16		ns
Rise Time	t_r					Tj=25℃ Tj=125℃		2 2		
Turn off delay time	$t_{d(OFF)}$					Tj=25℃ Tj=125℃		103 113		
Fall time	t_f					Tj=25℃ Tj=125℃		6 9		
Turn-on energy loss per pulse	E_{on}					Tj=25℃ Tj=125℃		0,045 0,091		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25℃ Tj=125℃		0,006 0,007		
Total gate charge	Q_{GE}		0/10	480	9,5	Tj=25℃		63		nC
Gate to source charge	Q_{GS}							7,6		
Gate to drain charge	Q_{GD}							32		
Input capacitance	C_{iss}	f=1MHz	0	100		Tj=25℃		1400		pF
Output capacitance	C_{oss}							85		
Gate resistance	R_G							6		Ω
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,51		K/W
PFC Diode										
Forward voltage	V_F				6	Tj=25℃ Tj=125℃		2,83 1,66		V
Reverse leakage current	I_{rm}			600		Tj=25℃ Tj=125℃			50 500	µA
Peak recovery current	I_{RRM}	Rgon=4 Ω	10	400	6	Tj=25℃ Tj=125℃		29 31		A
Reverse recovery time	t_{rr}					Tj=25℃ Tj=125℃		9 15		ns
Reverse recovery charge	Q_{rr}					Tj=25℃ Tj=125℃		0,12 0,29		µC
Reverse recovered energy	E_{rec}					Tj=25℃ Tj=125℃		0,013 0,042		mWs
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25℃ Tj=125℃		12276 7905		A/µs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2,95		K/W
PFC Shunt										
R1 value	R							50		mΩ
Temperature coeficient	t_c	20℃ to 60℃							30	ppm/K
Internal heat resistance	R_{thi}								10	K/W
Inductance	L								3	nH

Characteristic Values

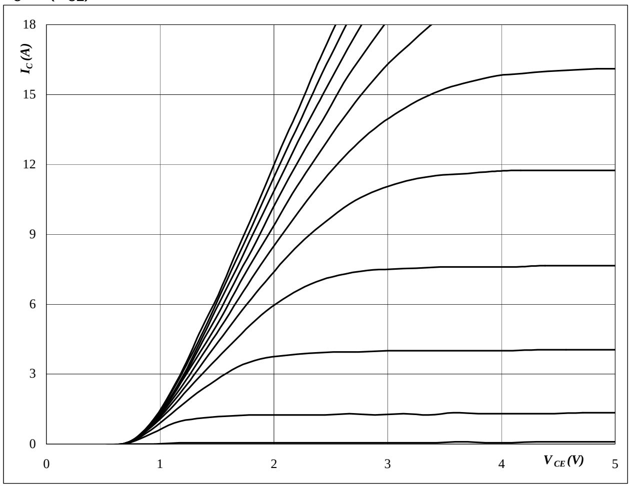
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Inverter Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,00009	Tj=25℃ Tj=125℃	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		6	Tj=25℃ Tj=125℃		1,52 1,71		V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	600		Tj=25℃ Tj=125℃			0,027	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25℃ Tj=125℃			300	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=64 Ω Rgon=64 Ω	±15	400	6	Tj=25℃ Tj=125℃		103 101		ns
Rise time	t_r					Tj=25℃ Tj=125℃		23 26		
Turn-off delay time	$t_{d(off)}$					Tj=25℃ Tj=125℃		154 177		
Fall time	t_f					Tj=25℃ Tj=125℃		96 105		
Turn-on energy loss per pulse	E_{on}					Tj=25℃ Tj=125℃		0,19 0,25		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25℃ Tj=125℃		0,21 0,27		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25℃		368		pF
Output capacitance	C_{oss}							28		
Reverse transfer capacitance	C_{rss}							11		
Gate charge	Q_{Gate}		±15	480	6	Tj=25℃		42		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						3,38		K/W
Inverter Diode										
Diode forward voltage	V_F				6	Tj=25℃ Tj=125℃	1,25	1,62 1,53	1,95	V
Peak reverse recovery current	I_{RRM}	Rgon=64 Ω	±15	400	6	Tj=25℃ Tj=125℃		3 4		A
Reverse recovery time	t_{rr}					Tj=25℃ Tj=125℃		236 341		ns
Reverse recovered charge	Q_{rr}					Tj=25℃ Tj=125℃		0,32 0,60		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25℃ Tj=125℃		12 30		A/µs
Reverse recovered energy	Erec					Tj=25℃ Tj=125℃		0,09 0,17		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						4,44		K/W
DC link Capacitor										
C value	C							100		nF
Thermistor										
Rated resistance	R					T=25℃		22000		Ω
Deviation of R100	ŎR/R	R100=1486 Ω				T=100℃	-5		5	%
Power dissipation	P					T=25℃		210		mW
Power dissipation constant						T=25℃		3,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				T=25℃				K
B-value	$B_{(25/100)}$	Tol. ±3%				T=25℃		4000		K
Vincotech NTC Reference									A	

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



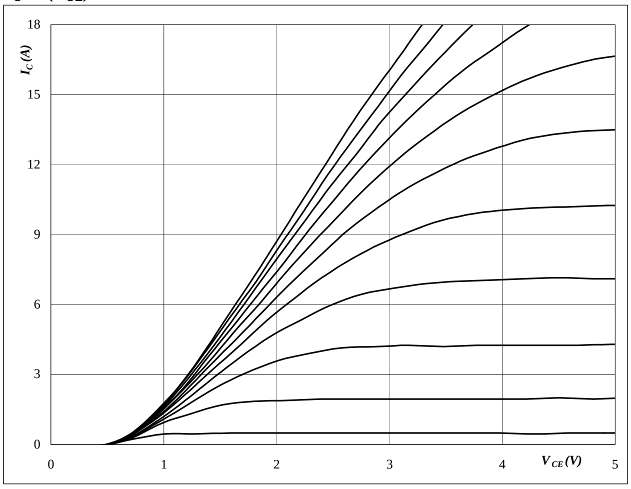
At

t_p =	250	μs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



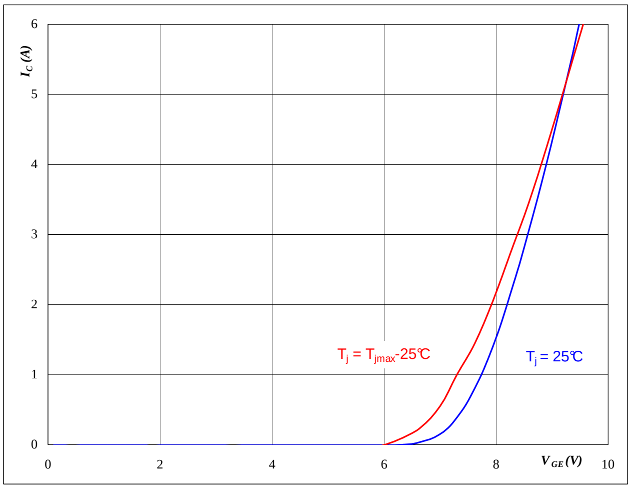
At

t_p =	250	μs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Output inverter IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



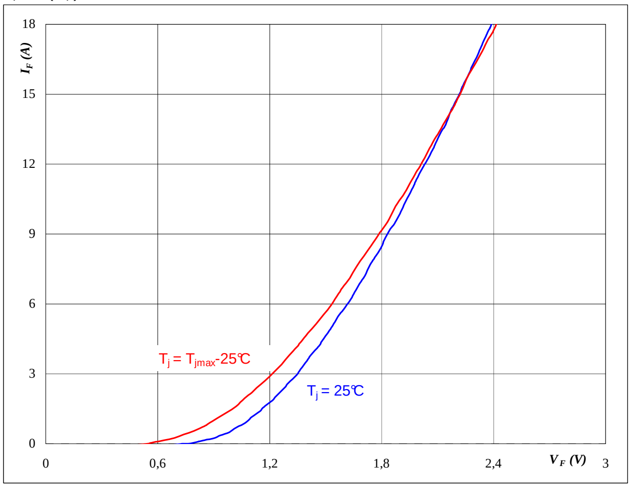
At

t_p =	250	μs
V_{CE} =	10	V

Figure 4 Output inverter FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



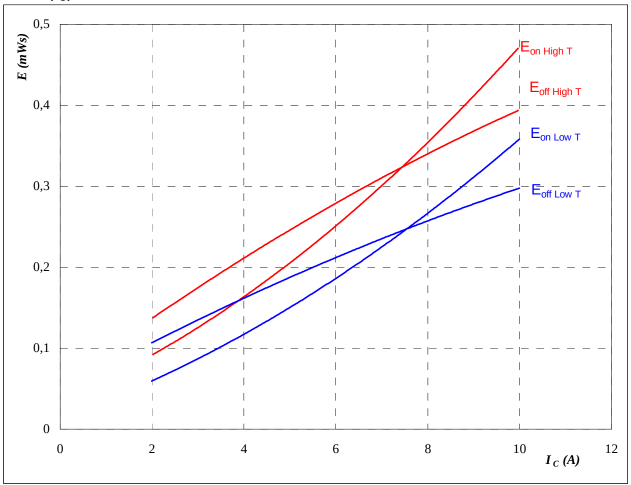
At

t_p =	250	μs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses
as a function of collector current
$E = f(I_C)$

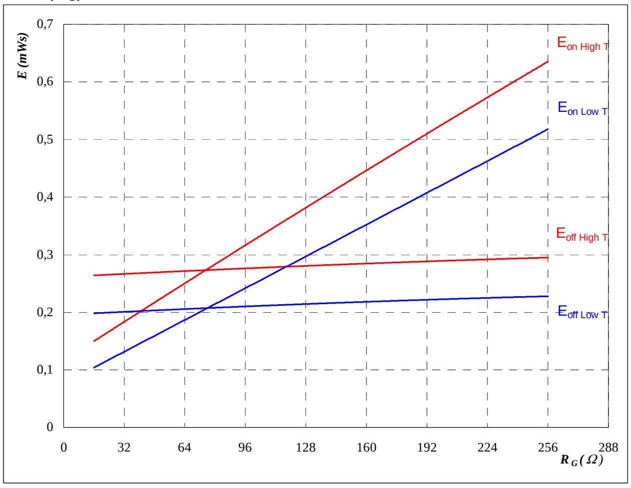


With an inductive load at

T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω
R_{goff} =	64	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses
as a function of gate resistor
$E = f(R_G)$

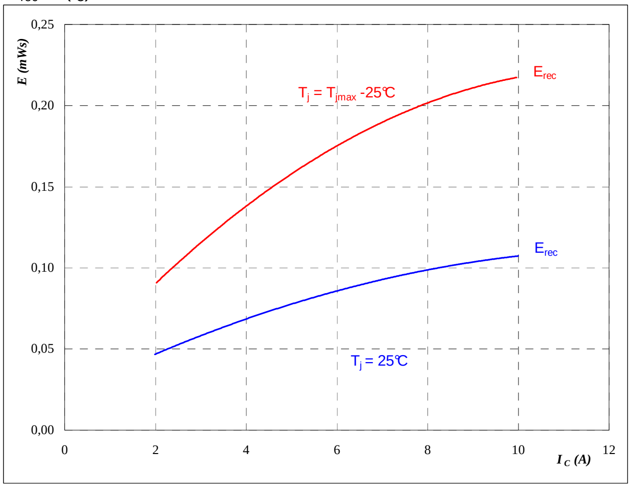


With an inductive load at

T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	±15	V
I_C =	6	A

Figure 7 Output inverter FWD

Typical reverse recovery energy loss
as a function of collector current
$E_{rec} = f(I_C)$

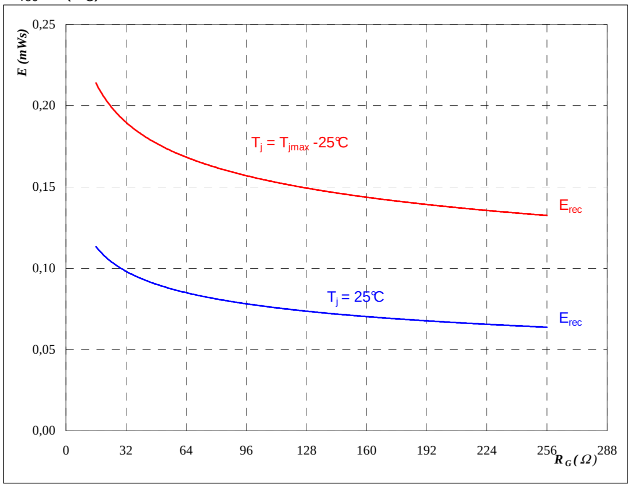


With an inductive load at

T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

Figure 8 Output inverter FWD

Typical reverse recovery energy loss
as a function of gate resistor
$E_{rec} = f(R_G)$



With an inductive load at

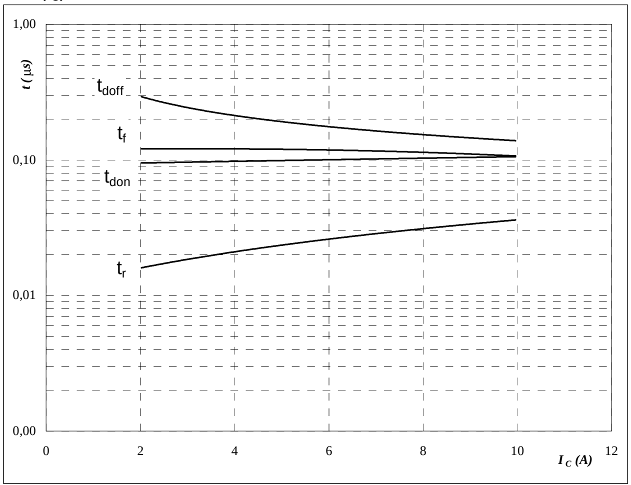
T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	±15	V
I_C =	6	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

t = f(I_C)



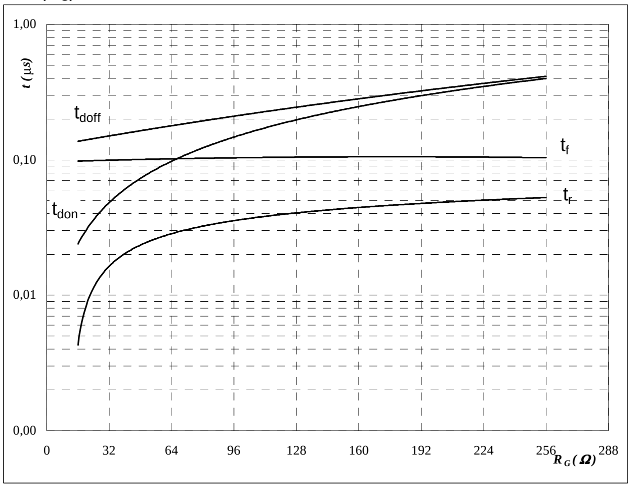
With an inductive load at

T_j =	125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω
R_{goff} =	64	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



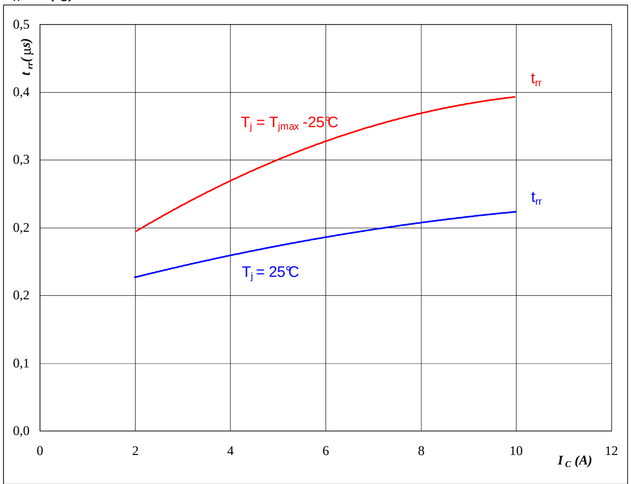
With an inductive load at

T_j =	125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
I_C =	6	A

Figure 11 Output inverter FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



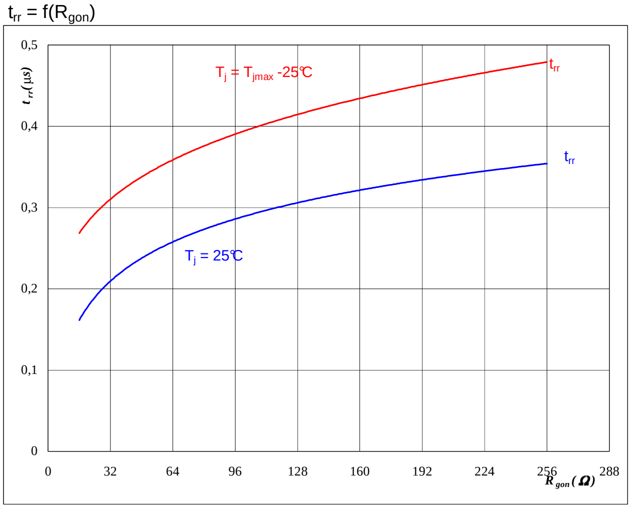
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

Figure 12 Output inverter FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

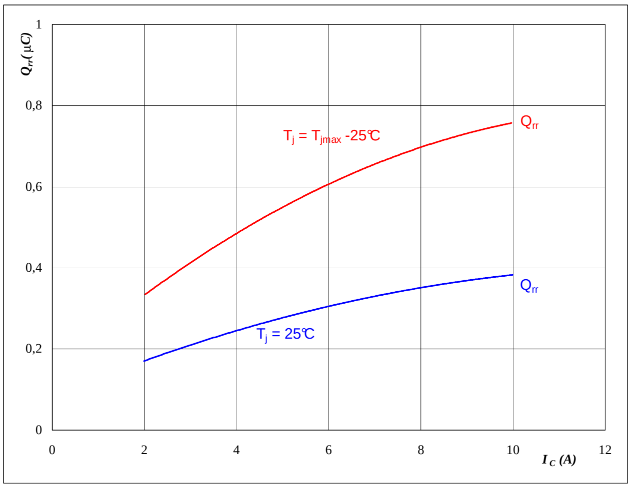
T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GE} =	±15	V

Output Inverter

Figure 13 Output inverter FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



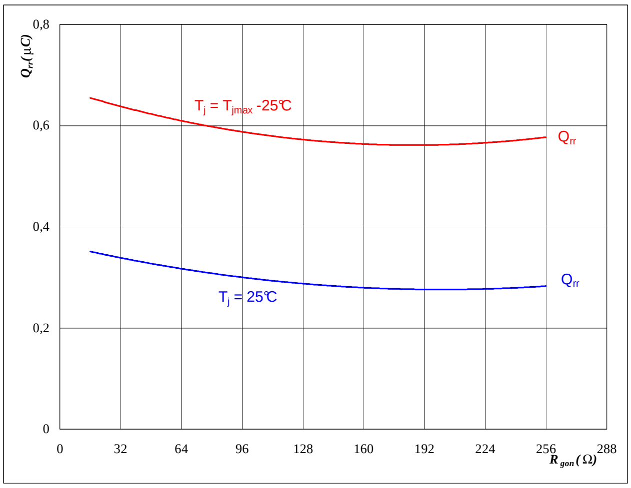
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

Figure 14 Output inverter FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



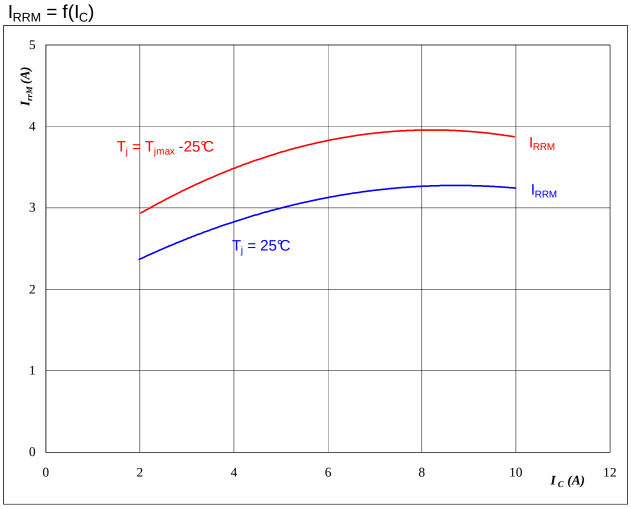
At

T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GE} =	±15	V

Figure 15 Output inverter FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



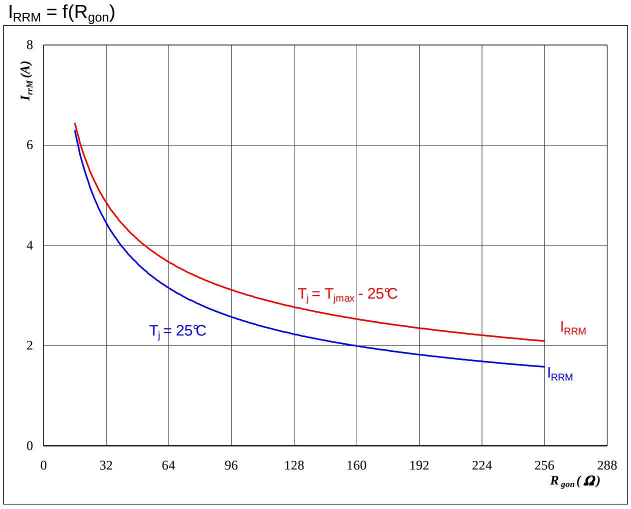
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

Figure 16 Output inverter FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

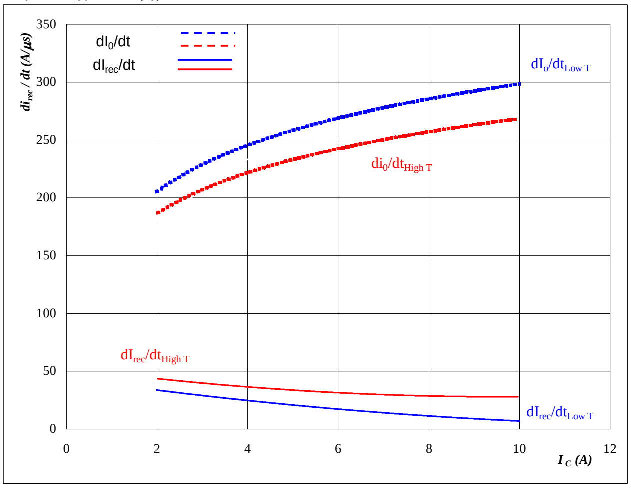
T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GE} =	±15	V

Output Inverter

Figure 17 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



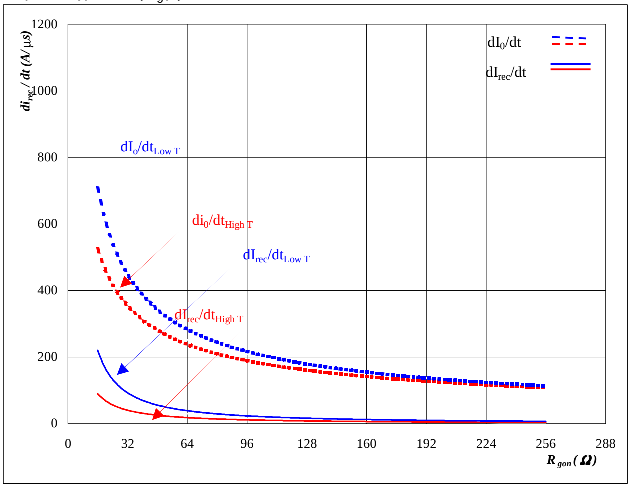
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	±15	V
R_{gon} =	64	Ω

Figure 18 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



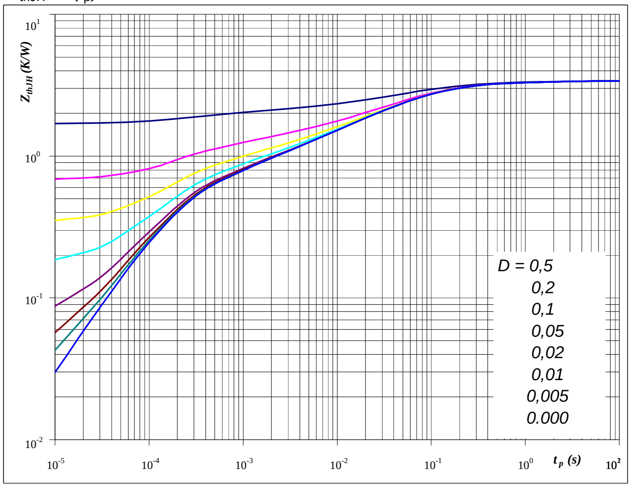
At

T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GE} =	±15	V

Figure 19 Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	3,38	K/W	RthJH =	2,74	K/W

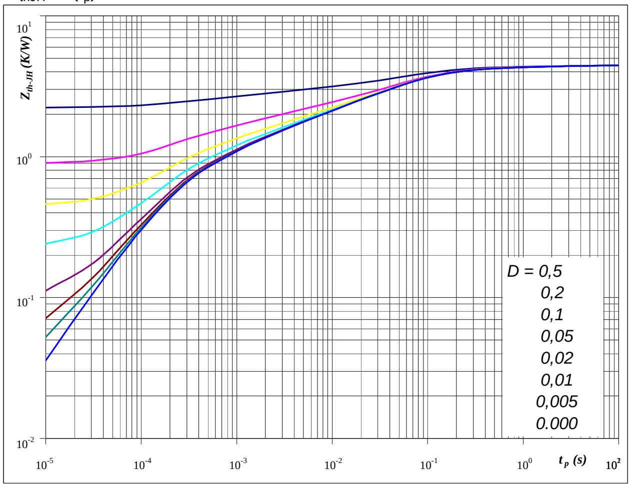
IGBT thermal model values

Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,16	1,710	0,13	1,387
0,70	0,168	0,56	0,136
1,11	0,044	0,90	0,036
0,55	0,008	0,45	0,007
0,34	0,001	0,27	0,001
0,53	0,000	0,43	0,000

Figure 20 Output inverter FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	4,44	K/W	RthJH =	3,60	K/W

FWD thermal model values

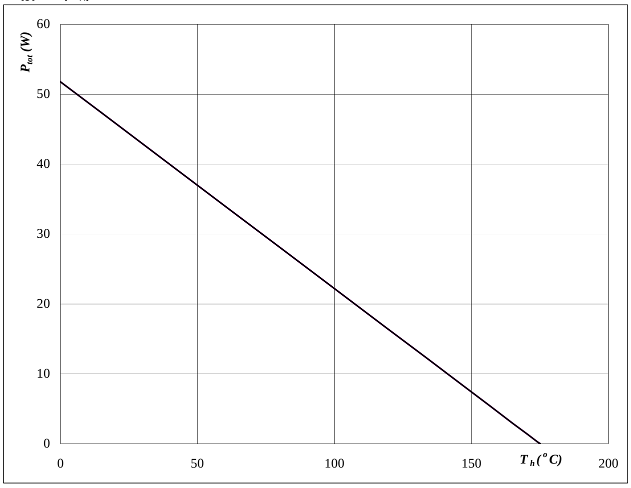
Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,20	1,973	0,16	1,600
0,90	0,162	0,73	0,131
1,46	0,039	1,18	0,032
0,65	0,007	0,53	0,005
0,56	0,001	0,46	0,001
0,67	0,000	0,54	0,000

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



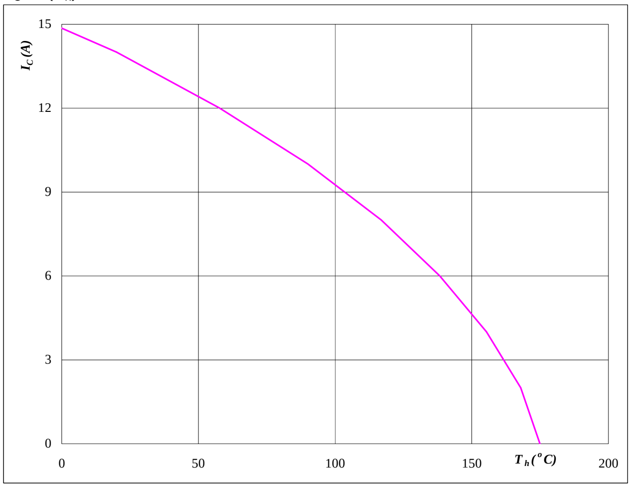
At

T_j = 175 ℃

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

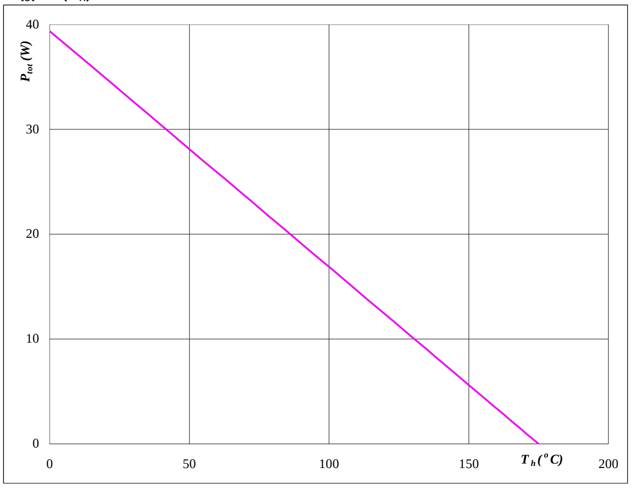
T_j = 175 ℃

V_{GE} = 15 V

Figure 23 Output inverter FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



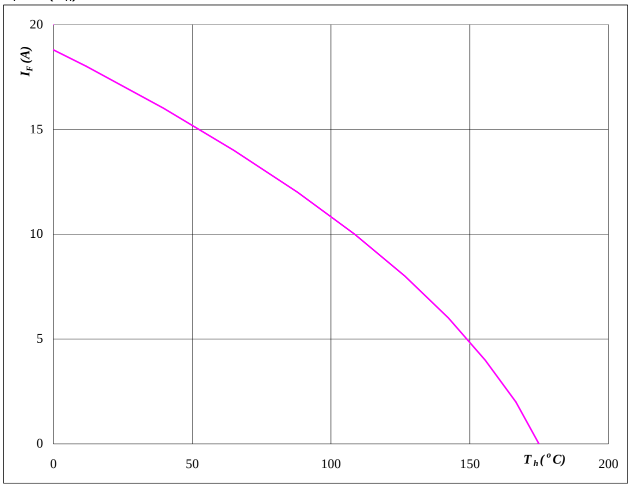
At

T_j = 175 ℃

Figure 24 Output inverter FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

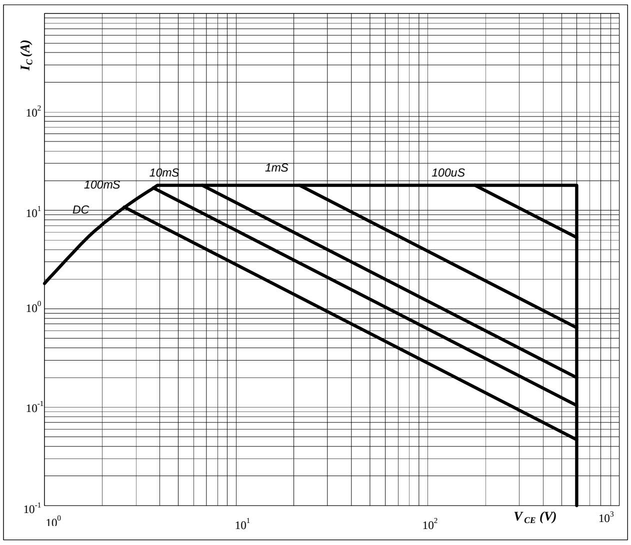
T_j = 175 ℃

Output Inverter

Figure 25	Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



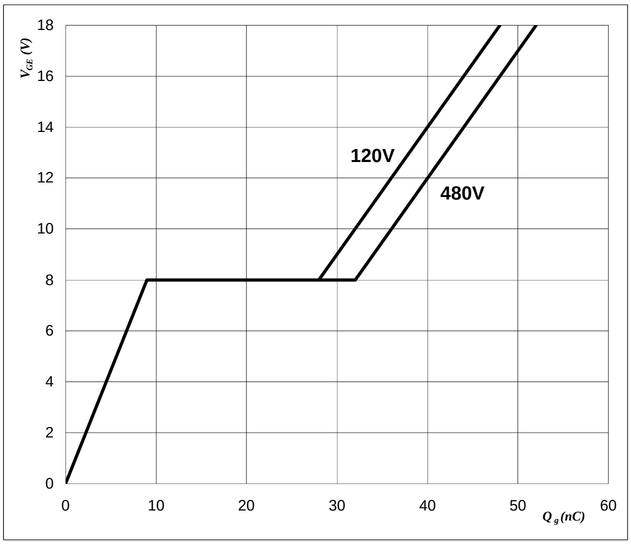
At

D =	single pulse	
T_h =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26	Output inverter IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_{GE})$



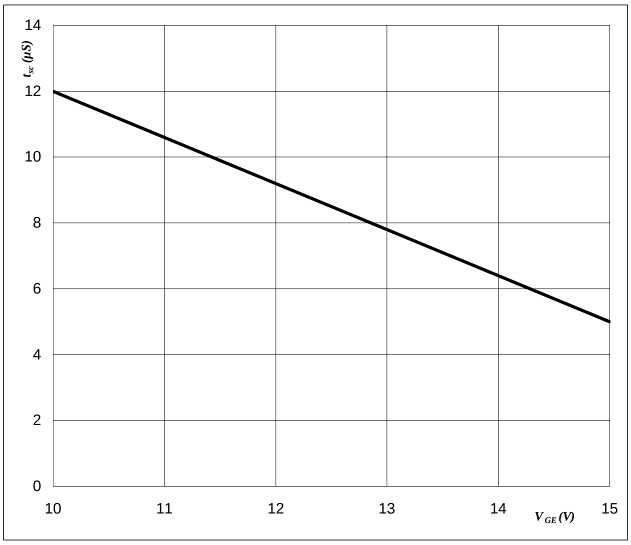
At

I_C =	6	A

Figure 27	Output inverter IGBT

Short circuit withstand time as a function of gate-emitter voltage

$t_{sc} = f(V_{GE})$



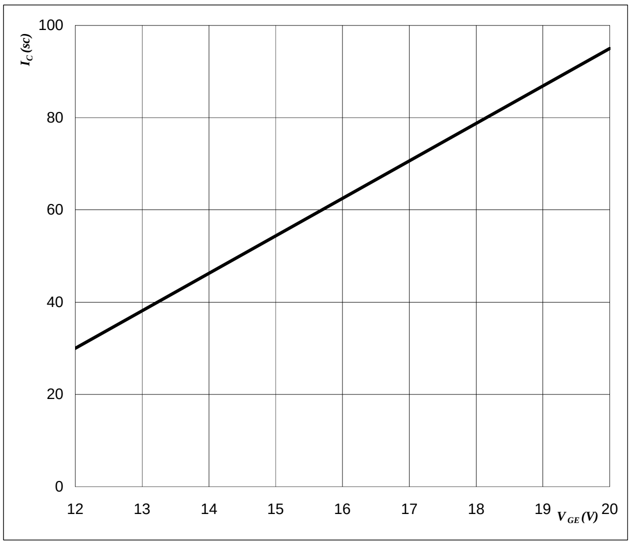
At

V_{CE} =	600	V
T_j ≤	175	ºC

Figure 28	Output inverter IGBT

Typical short circuit collector current as a function of gate-emitter voltage

$V_{GE} = f(Q_{GE})$



At

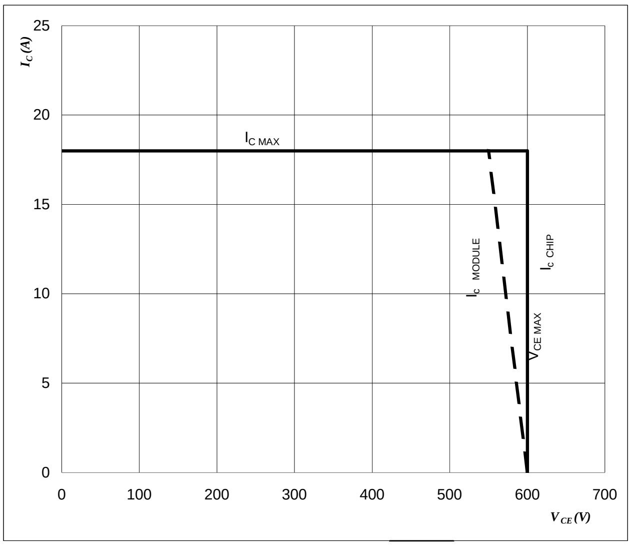
V_{CE} ≤	600	V
T_j =	175	ºC

Output Inverter

Figure 29 IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

$U_{ccminus}$=U_{ccplus}

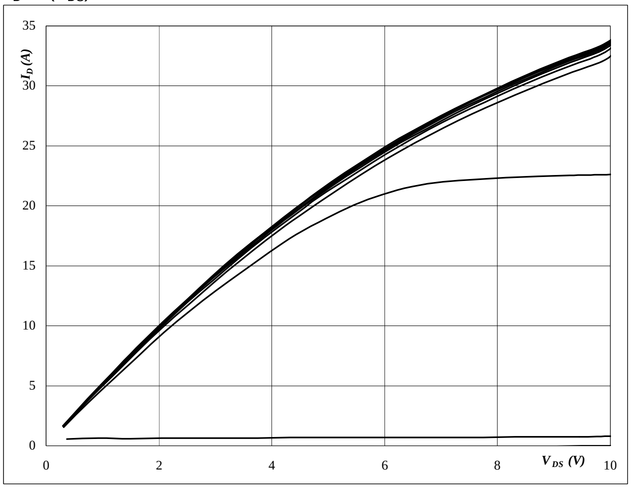
Switching mode : 3phase SPWM

PFC

Figure 1 PFC MOSFET

Typical output characteristics

$I_D = f(V_{DS})$



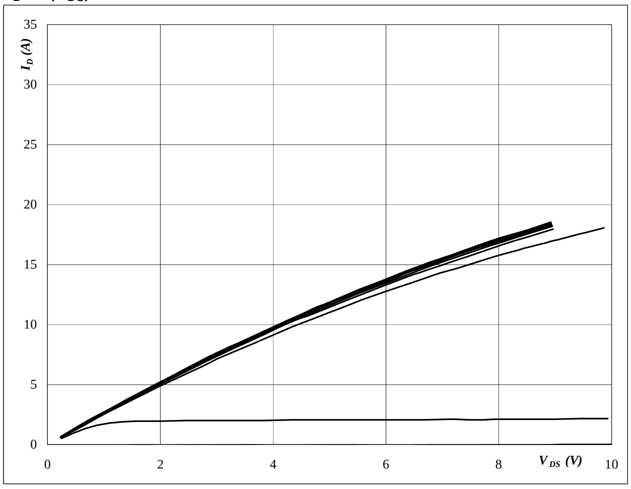
At

t_p =	250	μs
T_j =	25	℃
V_{GS} from	0 V to 20 V in steps of 2 V	

Figure 2 PFC MOSFET

Typical output characteristics

$I_D = f(V_{DS})$



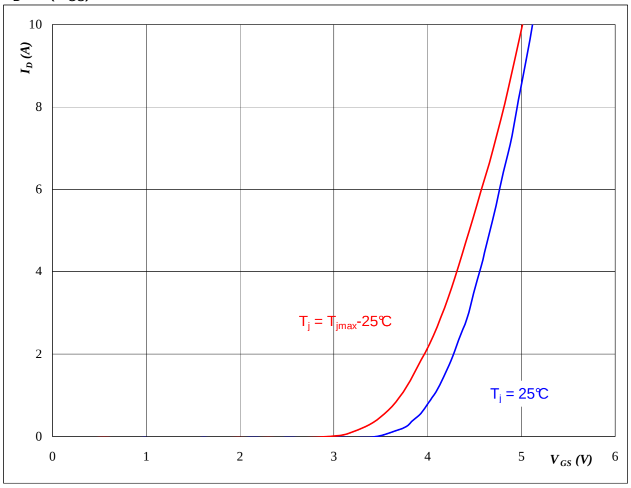
At

t_p =	250	μs
T_j =	125	℃
V_{GS} from	0 V to 20 V in steps of 2 V	

Figure 3 PFC MOSFET

Typical transfer characteristics

$I_D = f(V_{GS})$



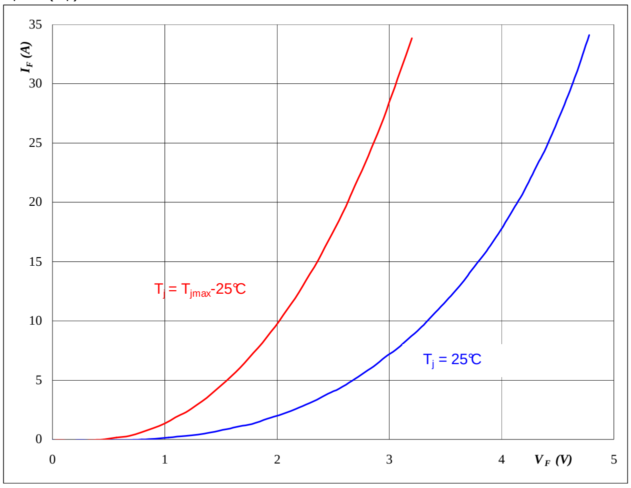
At

t_p =	250	μs
V_{DS} =	10	V

Figure 4 PFC FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

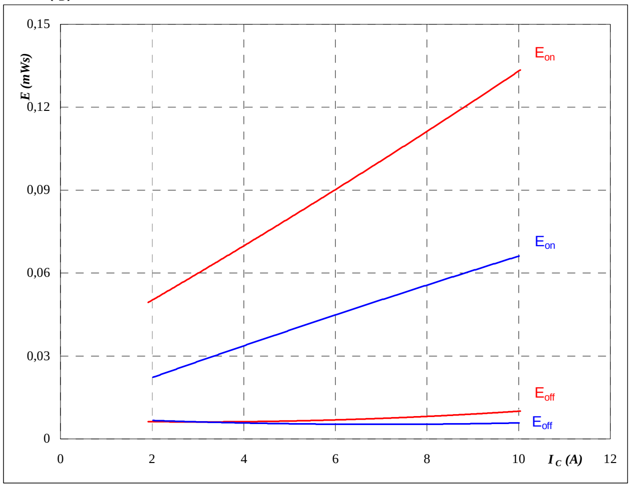
t_p =	250	μs

PFC

Figure 5 PFC MOSFET

Typical switching energy losses as a function of collector current

$E = f(I_D)$



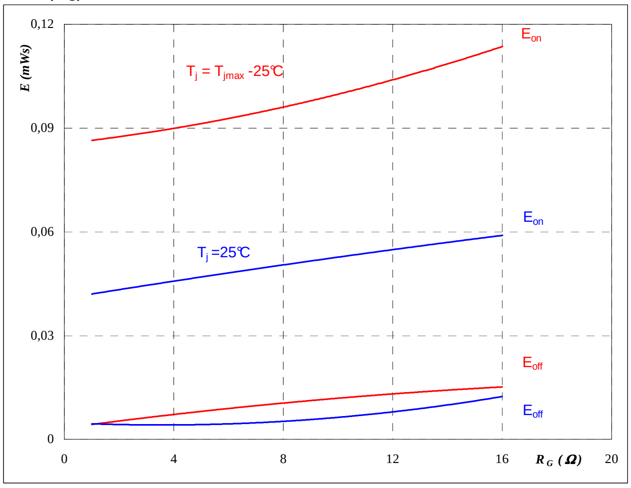
With an inductive load at

T_j =	25/125	℃
V_{DS} =	400	V
V_{GS} =	10	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 6 PFC MOSFET

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$



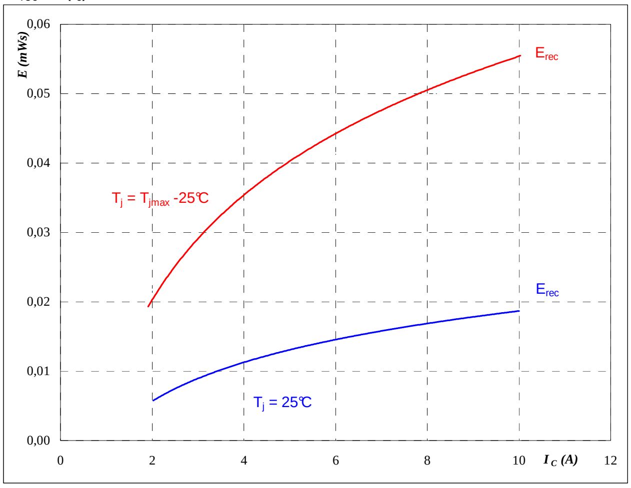
With an inductive load at

T_j =	25/125	℃
V_{DS} =	400	V
V_{GS} =	10	V
I_D =	6	A

Figure 7 PFC MOSFET

Typical reverse recovery energy loss as a function of collector (drain) current

$E_{rec} = f(I_c)$



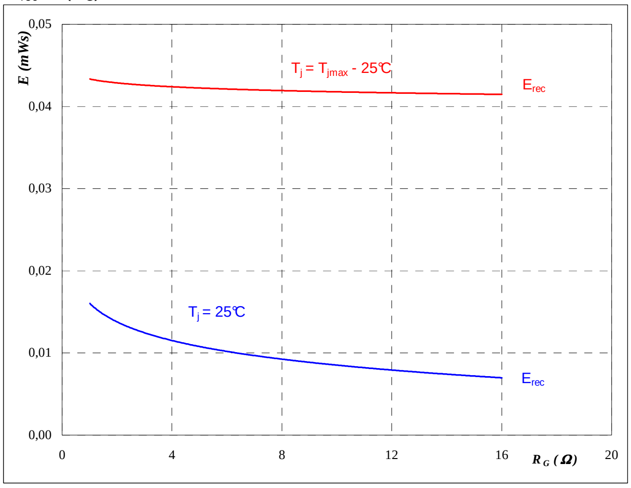
With an inductive load at

T_j =	25/125	℃
V_{DS} =	400	V
V_{GS} =	10	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 8 PFC MOSFET

Typical reverse recovery energy loss as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

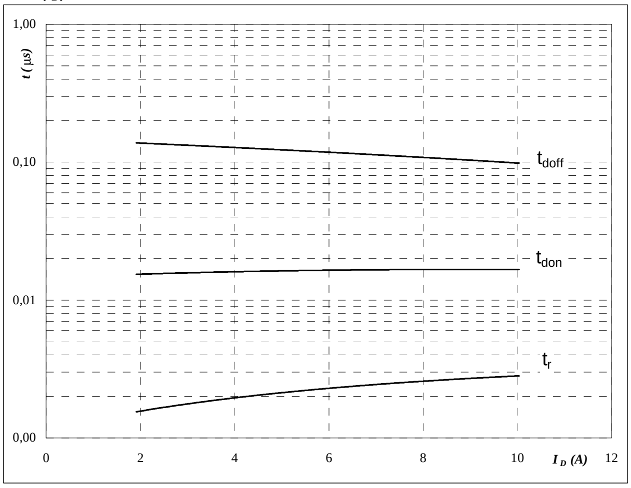
T_j =	25/125	℃
V_{DS} =	400	V
V_{GS} =	10	V
I_D =	6	A

PFC

Figure 9 PFC MOSFET

Typical switching times as a function of collector current

t = f(I_D)



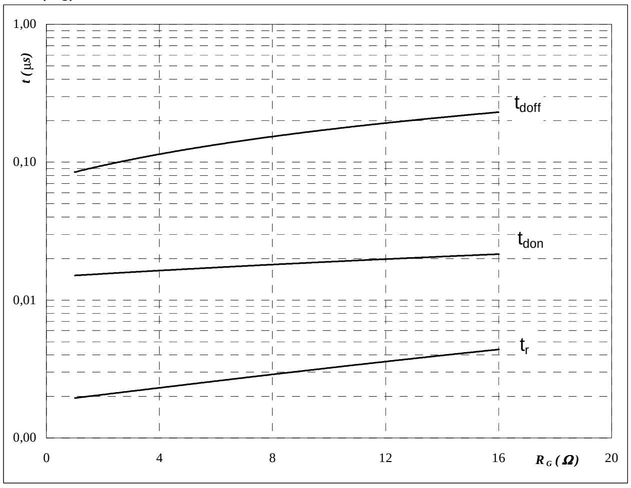
With an inductive load at

T_j =	125	℃
V_{DS} =	400	V
V_{GS} =	10	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 10 PFC MOSFET

Typical switching times as a function of gate resistor

t = f(R_G)



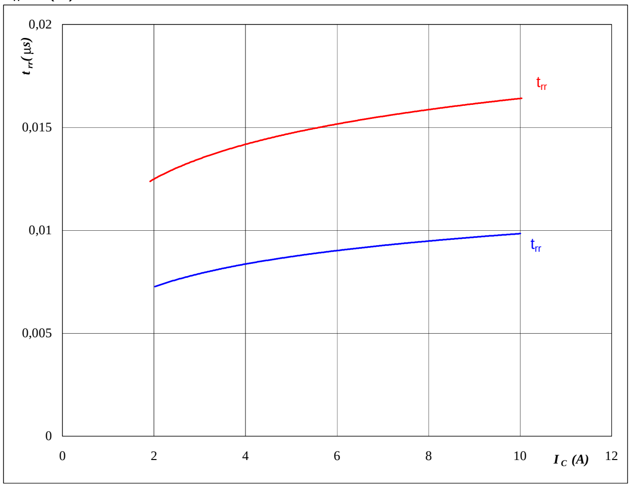
With an inductive load at

T_j =	125	℃
V_{DS} =	400	V
V_{GS} =	10	V
I_C =	6	A

Figure 11 PFC FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(Ic)



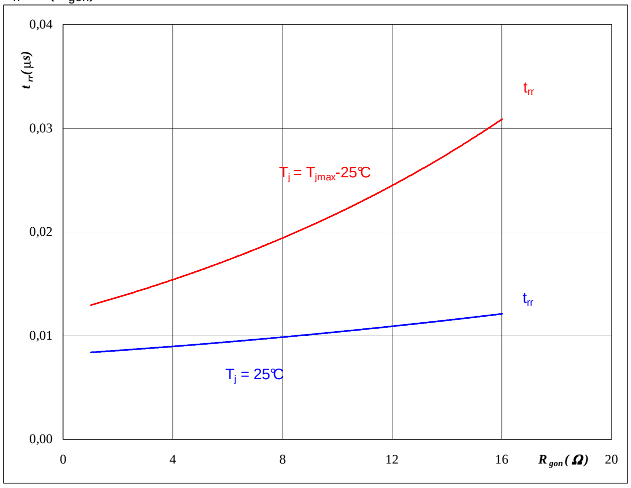
At

T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	10	V
R_{gon} =	4,01	Ω

Figure 12 PFC FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

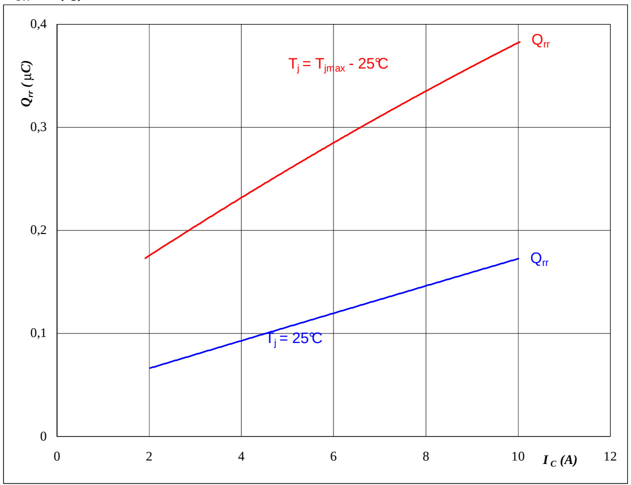
T_j =	25/125	℃
V_R =	400	V
I_F =	6	A
V_{GS} =	10	V

PFC

Figure 13 PFC FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



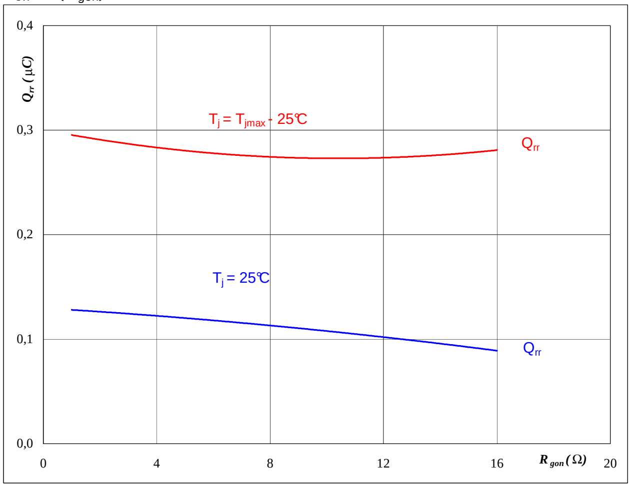
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	10	V
R_{gon} =	4	Ω

Figure 14 PFC FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



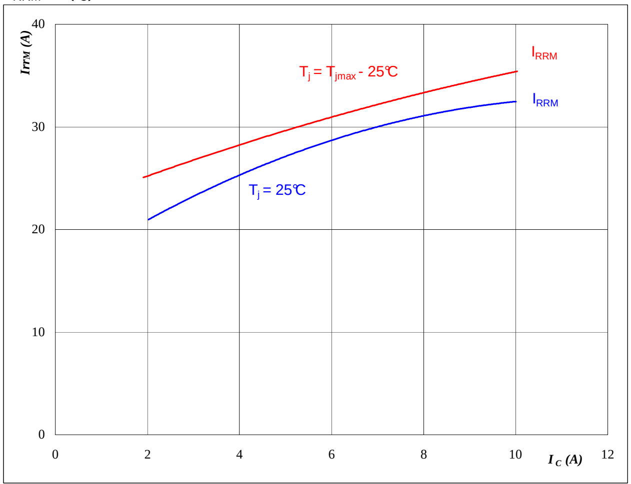
At

T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GS} =	10	V

Figure 15 PFC FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



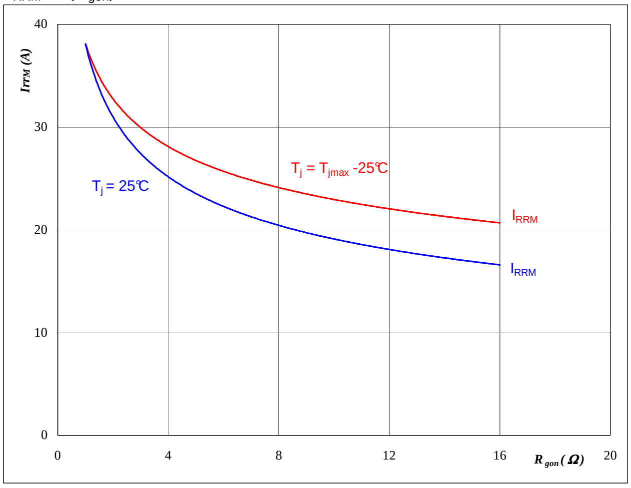
At

T_j =	25/125	°C
V_{CE} =	400	V
V_{GE} =	10	V
R_{gon} =	4	Ω

Figure 16 PFC FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

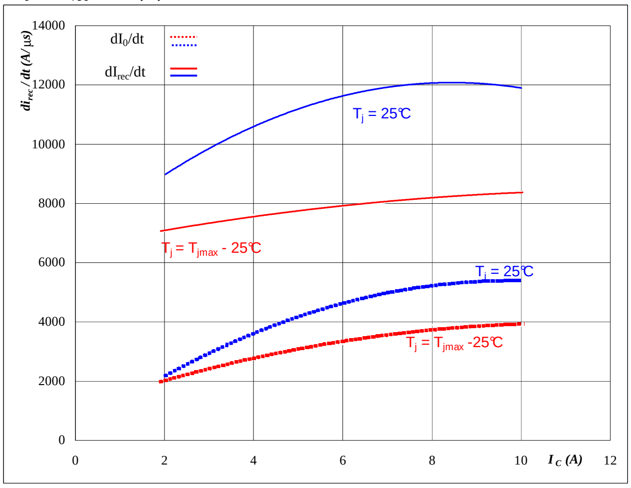
T_j =	25/125	°C
V_R =	400	V
I_F =	6	A
V_{GS} =	10	V

PFC

Figure 17 PFC FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(Ic)$



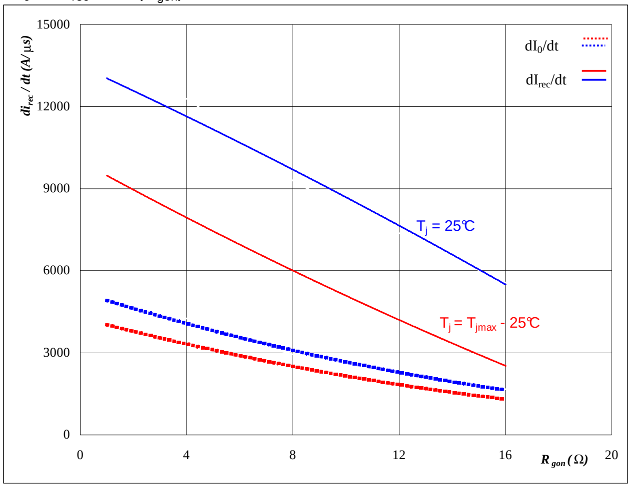
At

T_j =	25/125	℃
V_{CE} =	400	V
V_{GE} =	10	V
R_{gon} =	4	Ω

Figure 18 PFC FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



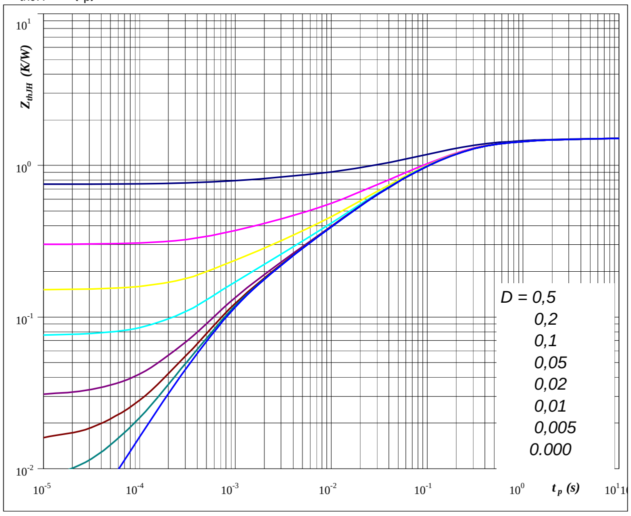
At

T_j =	25/125	℃
V_R =	400	V
I_F =	6	A
V_{GS} =	10	V

Figure 19 PFC MOSFET

IGBT/MOSFET transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	1,51	K/W	R_{thJH} =	1,22	K/W

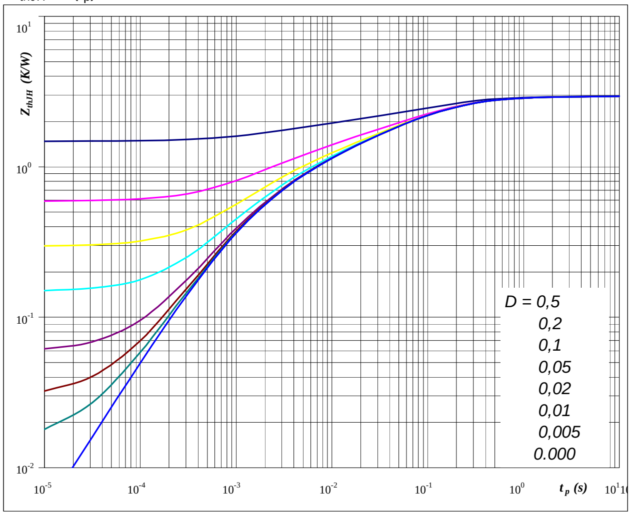
IGBT thermal model values

Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,07	2,94	0,06	2,38
0,21	0,46	0,17	0,37
0,65	0,12	0,53	0,09
0,31	0,03	0,25	0,02
0,15	0,01	0,12	0,01
0,11	0,00	0,09	0,00

Figure 20 PFC FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	2,95	K/W	R_{thJH} =	2,39	K/W

FWD thermal model values

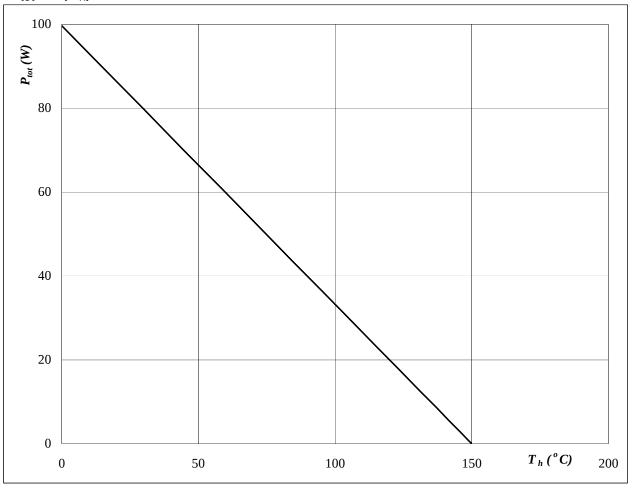
Thermal grease		Phase change interface	
R (C/W)	Tau (s)	R (C/W)	Tau (s)
0,11	2,95	0,09	2,39
0,51	0,31	0,41	0,26
1,04	0,08	0,84	0,06
0,58	0,01	0,47	0,01
0,45	0,00	0,37	0,00
0,27	0,00	0,22	0,00

PFC

Figure 21 PFC MOSFET

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



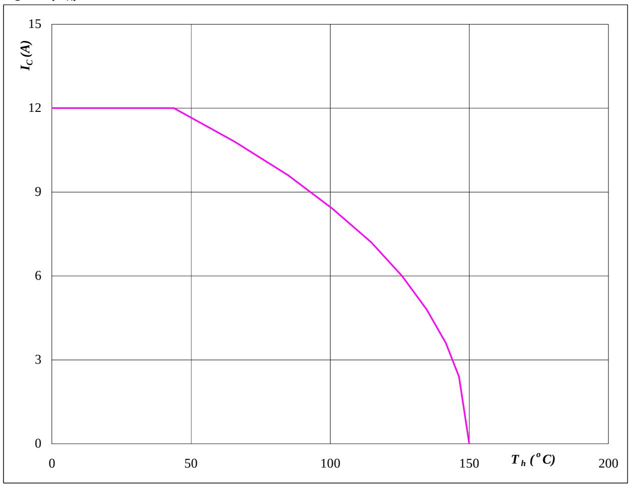
At

T_j = 150 ºC

Figure 22 PFC MOSFET

Collector/Drain current as a function of heatsink temperature

$I_C = f(T_h)$



At

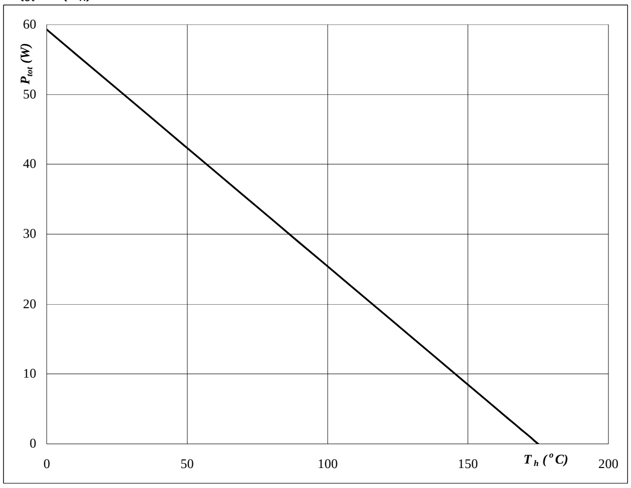
T_j = 150 ºC

V_{GS} = 10 V

Figure 23 PFC FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



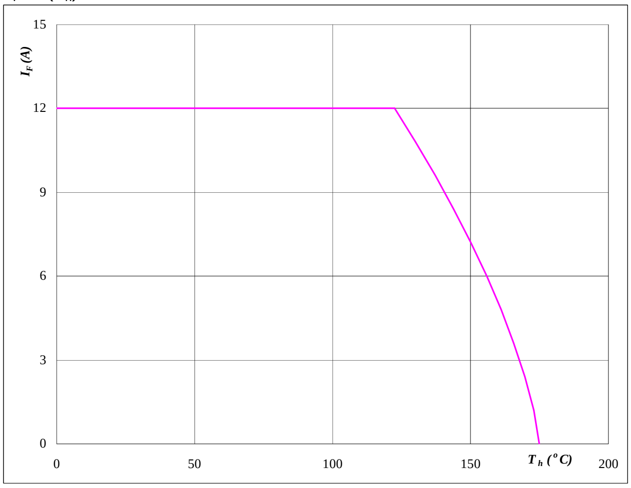
At

T_j = 175 ºC

Figure 24 PFC FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

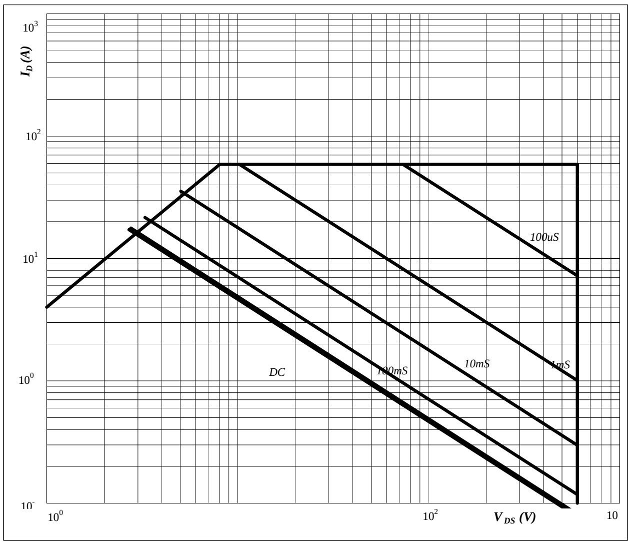
T_j = 175 ºC

PFC

Figure 25 PFC MOSFET

Safe operating area as a function of drain-source voltage

$I_D = f(V_{DS})$



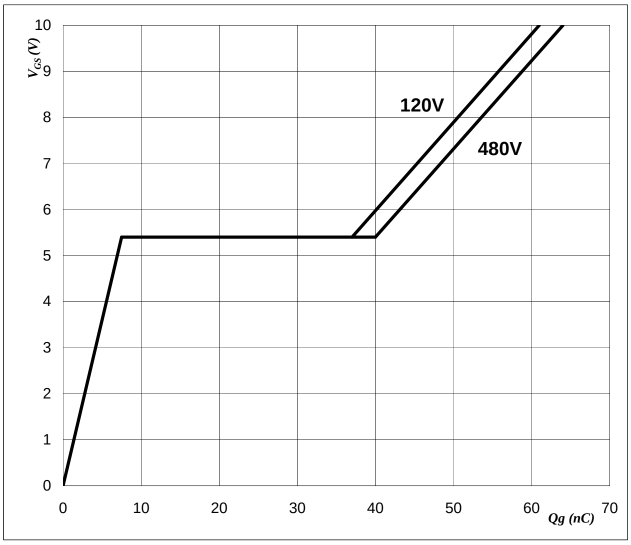
At

D =	single pulse	
T_h =	80	ºC
V_{GS} =	10	V
T_j =	T_{jmax}	ºC

Figure 26 PFC MOSFET

Gate voltage vs Gate charge

$V_{GS} = f(Qg)$



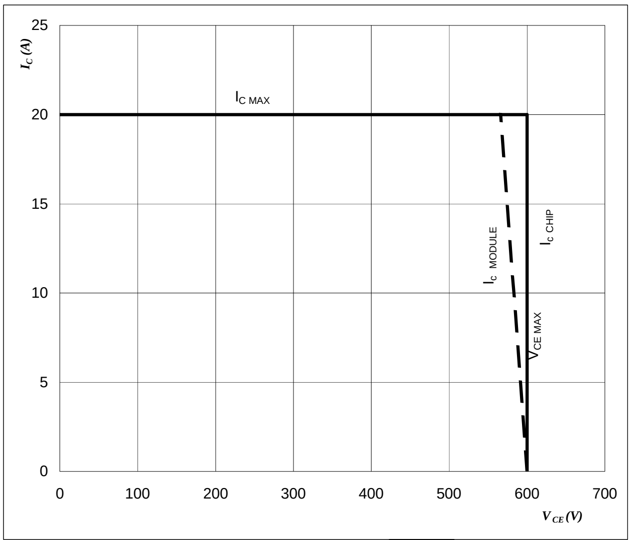
At

I_D =	6	A

Figure 29 IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

$U_{ccminus}$=U_{ccplus}

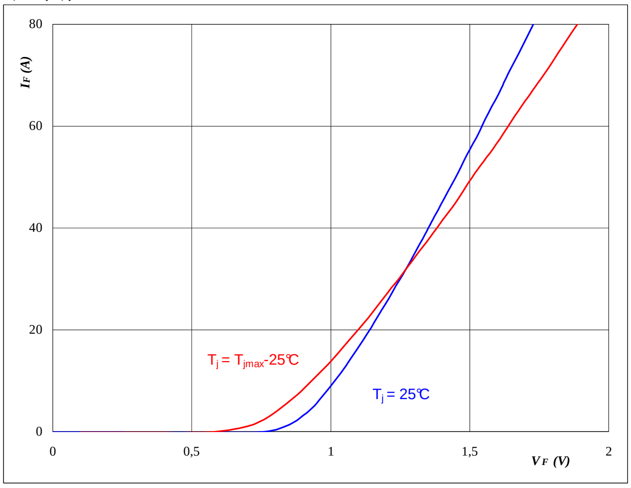
Switching mode : 3phase SPWM

Input Rectifier Bridge

Figure 1 Rectifier diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



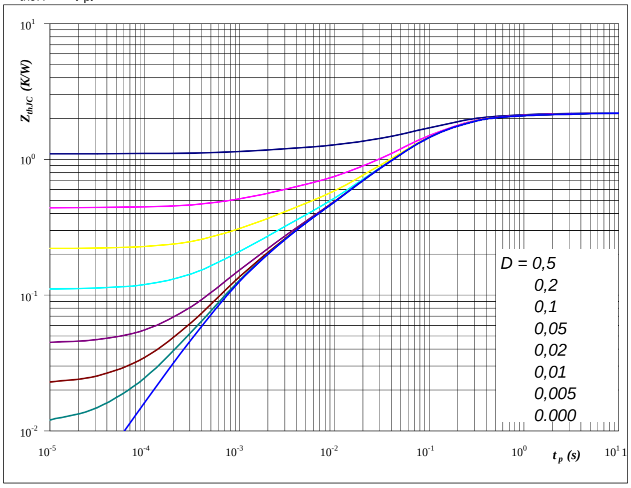
At

t_p =	250	μs

Figure 2 Rectifier diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



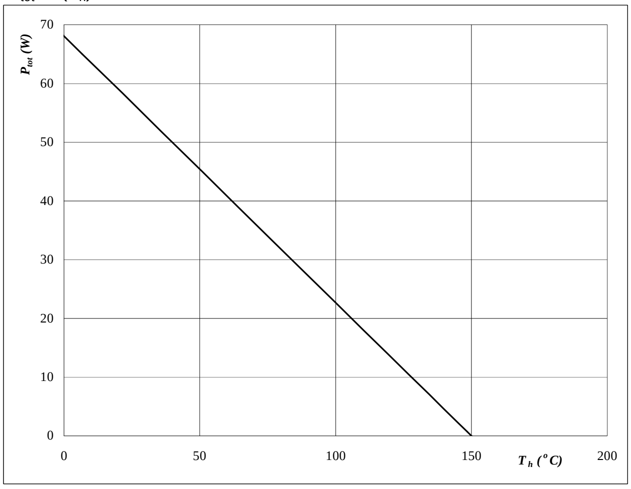
At

D =	t_p / T	
R_{thJH} =	2,20	K/W

Figure 3 Rectifier diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



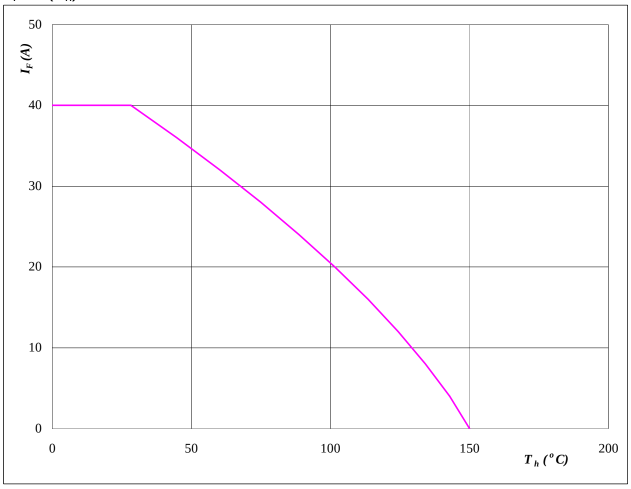
At

T_j =	150	ºC

Figure 4 Rectifier diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

T_j =	150	ºC

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature
$R_T = f(T)$

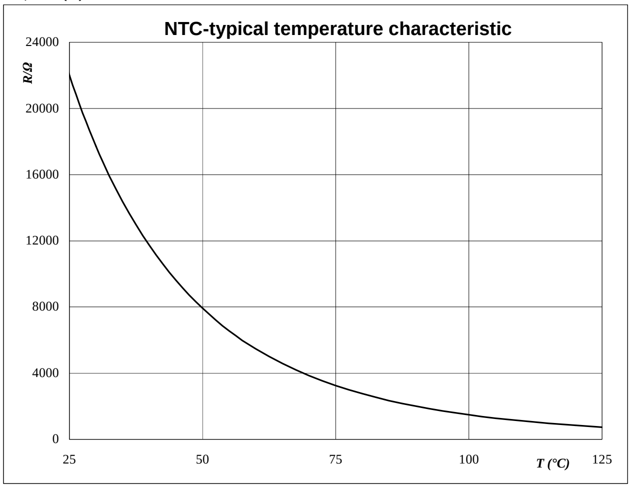


Figure 2 Thermistor

Typical NTC resistance values

$$R(T) = R_{25} \cdot e^{\left(B_{25/100} \cdot \left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right)} \quad [\Omega]$$

T [°C]	R_{nom} [Ω]	R_{min} [Ω]	R_{max} [Ω]	△R/R [±%]
-55	2089434,5	1506495,4	2672373,6	27,9
0	71804,2	59724,4	83884	16,8
10	43780,4	37094,4	50466,5	15,3
20	27484,6	23684,6	31284,7	13,8
25	22000	19109,3	24890,7	13,1
30	17723,3	15512,2	19934,4	12,5
60	5467,9	4980,6	5955,1	8,9
70	3848,6	3546	4151,1	7,9
80	2757,7	2568,2	2947,1	6,9
90	2008,9	1889,7	2128,2	5,9
100	**1486,1**	**1411,8**	**1560,4**	**5**
150	400,2	364,8	435,7	8,8

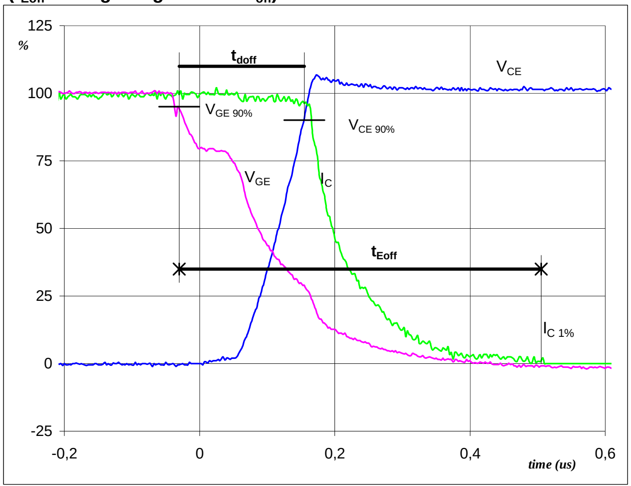
Switching Definitions Output Inverter

General conditions

T_j	=	125 °C
R_{gon}	=	64 Ω
R_{goff}	=	64 Ω

Figure 1 Output inverter IGBT

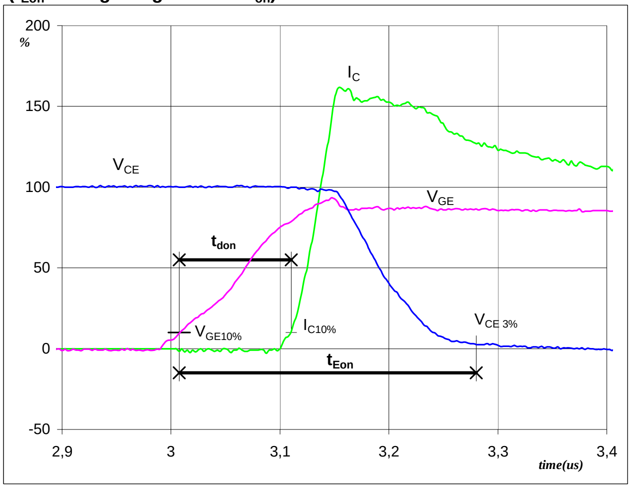
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	400	V
I_C (100%) =	6	A
t_{doff} =	0,18	μs
t_{Eoff} =	0,54	μs

Figure 2 Output inverter IGBT

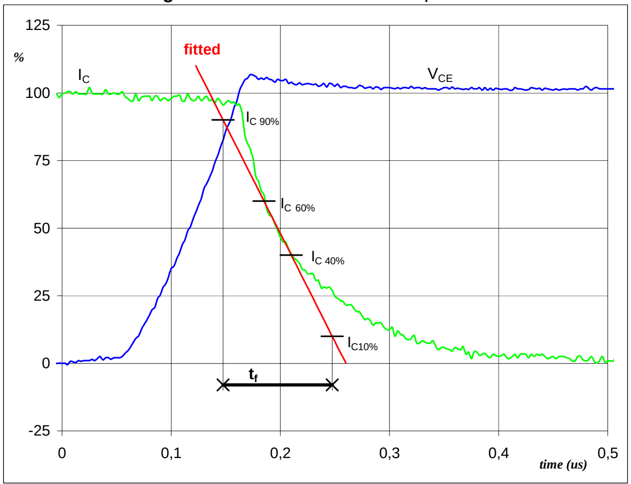
Turn-on Switching Waveforms & definition of tdon, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	400	V
I_C (100%) =	6	A
t_{don} =	0,10	μs
t_{Eon} =	0,27	μs

Figure 3 Output inverter IGBT

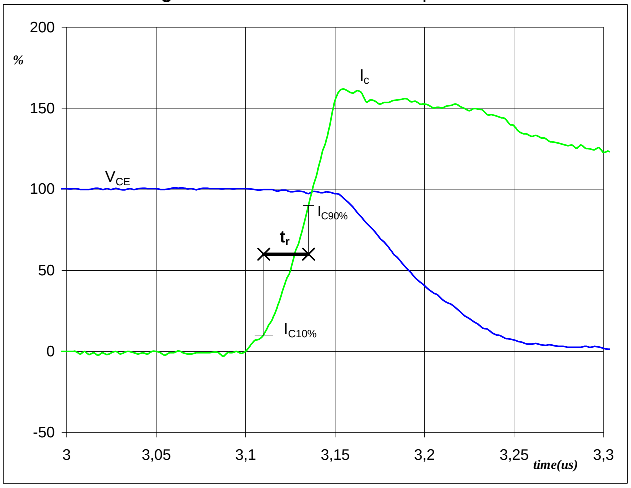
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	400	V
I_C (100%) =	6	A
t_f =	0,11	μs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

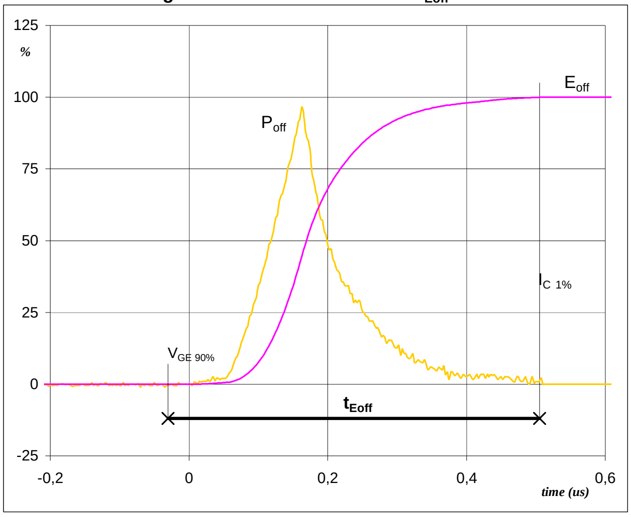


V_C (100%) =	400	V
I_C (100%) =	6	A
t_r =	0,03	μs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

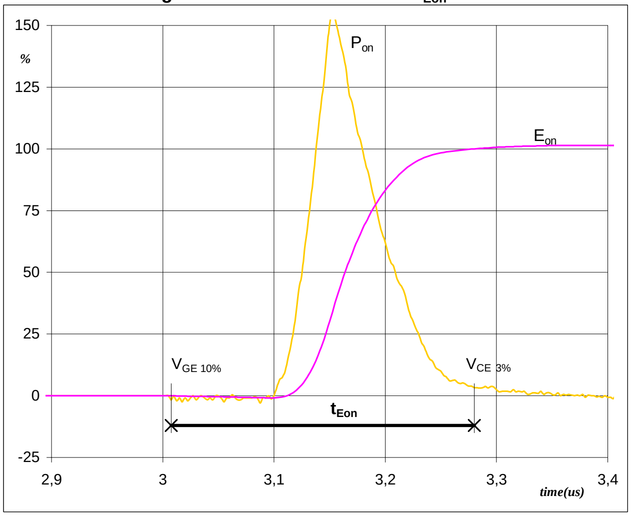
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	2,41	kW
E_{off} (100%) =	0,27	mJ
t_{Eoff} =	0,54	μs

Figure 6 Output inverter IGBT

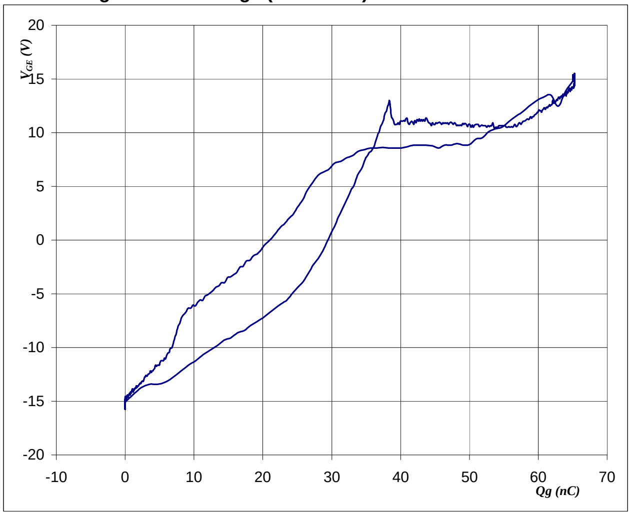
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	2,41	kW
E_{on} (100%) =	0,25	mJ
t_{Eon} =	0,27	μs

Figure 7 Output inverter IGBT

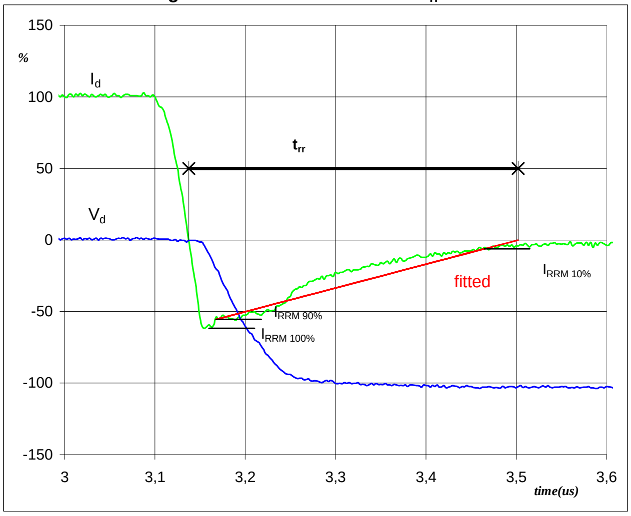
Gate voltage vs Gate charge (measured)



V_{GEoff} =	-15	V
V_{GEon} =	15	V
V_C (100%) =	400	V
I_C (100%) =	6	A
Q_g =	65,25	nC

Figure 8 Output inverter FWD

Turn-off Switching Waveforms & definition of t_{rr}

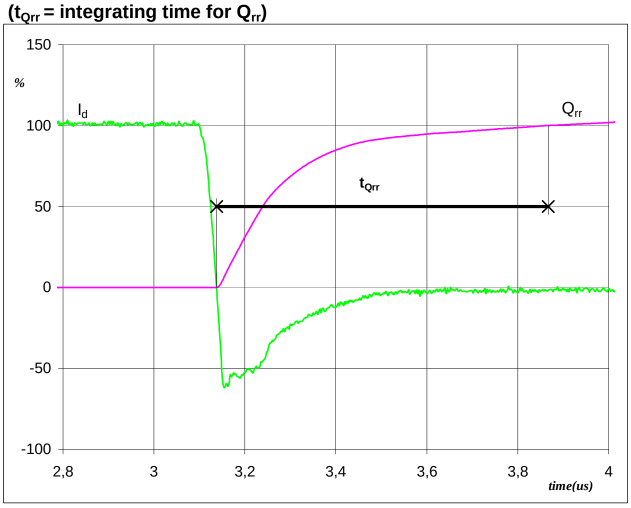


V_d (100%) =	400	V
I_d (100%) =	6	A
I_{RRM} (100%) =	-4	A
t_{rr} =	0,34	μs

Switching Definitions Output Inverter

Figure 9 Output inverter FWD

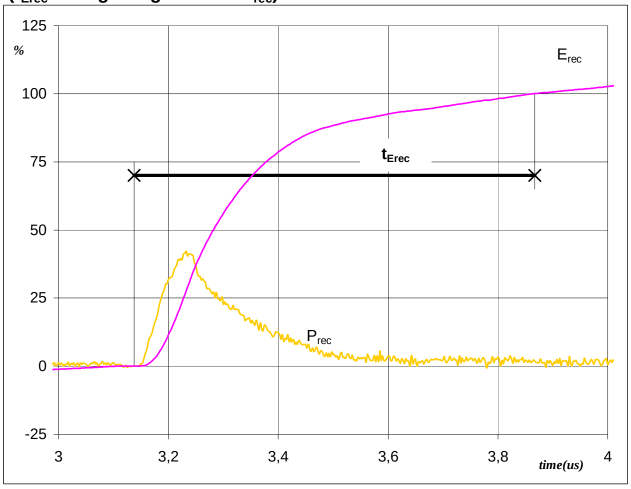
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	6	A
Q_{rr} (100%) =	0,60	µC
t_{Qrr} =	0,73	µs

Figure 10 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	2,41	kW
E_{rec} (100%) =	0,17	mJ
t_{Erec} =	0,73	µs

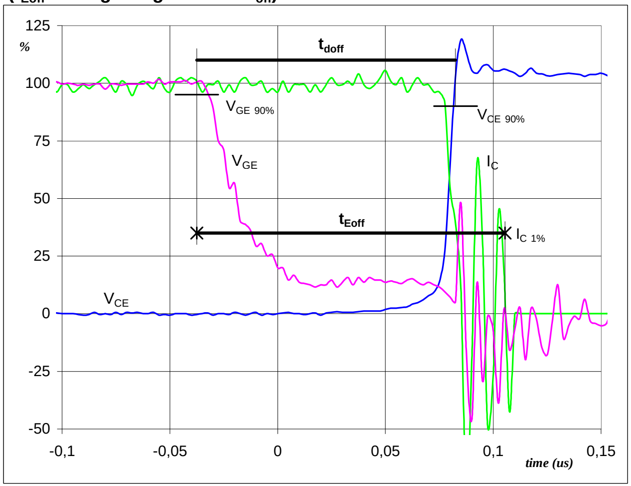
Switching Definitions PFC

General conditions

T_j	=	125 ℃
R_{gon}	=	4 Ω
R_{goff}	=	4 Ω

Figure 1 PFC MOSFET

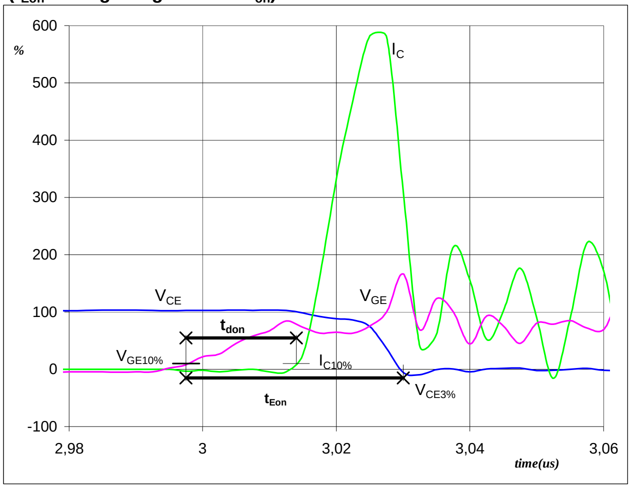
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	0	V
V_{GE} (100%) =	10	V
V_C (100%) =	400	V
I_C (100%) =	6	A
t_{doff} =	0,11	µs
t_{Eoff} =	0,14	µs

Figure 2 PFC MOSFET

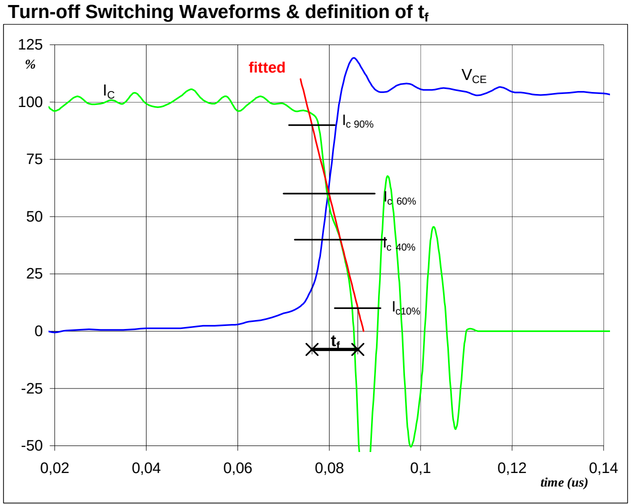
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	0	V
V_{GE} (100%) =	10	V
V_C (100%) =	400	V
I_C (100%) =	6	A
t_{don} =	0,02	µs
t_{Eon} =	0,03	µs

Figure 3 PFC MOSFET

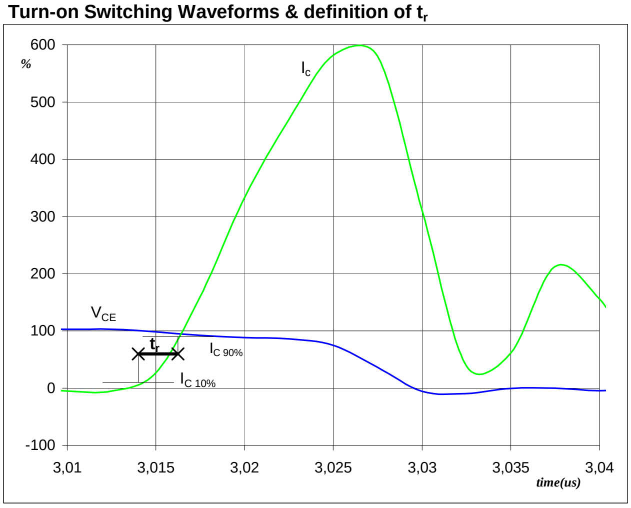
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	400	V
I_C (100%) =	6	A
t_f =	0,01	µs

Figure 4 PFC MOSFET

Turn-on Switching Waveforms & definition of t_r

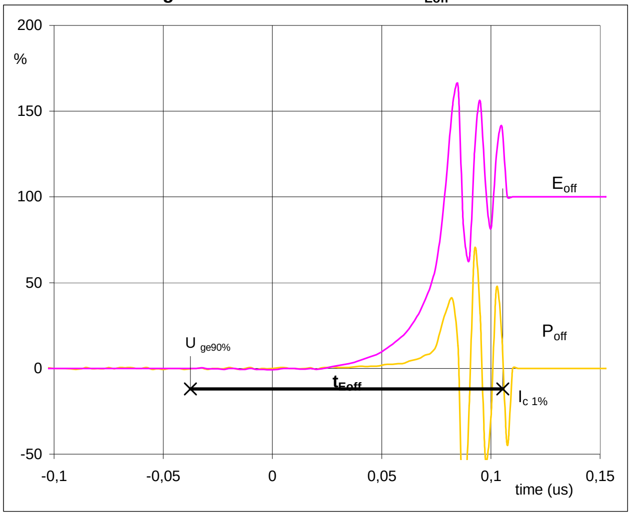


V_C (100%) =	400	V
I_C (100%) =	6	A
t_r =	0,002	µs

Switching Definitions PFC

Figure 5 PFC MOSFET

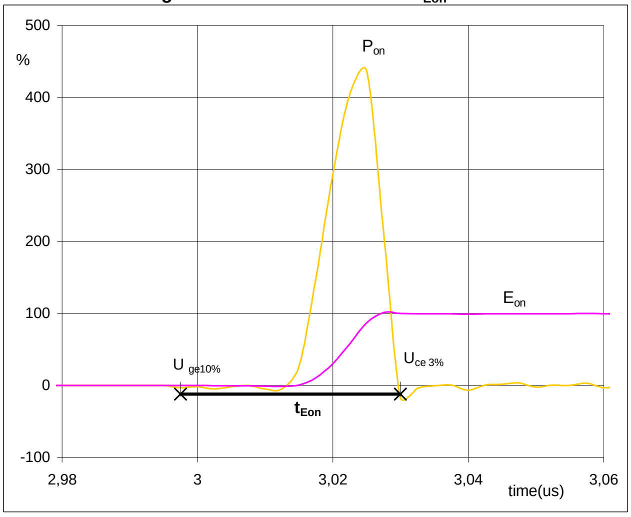
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	2,45	kW
E_{off} (100%) =	0,01	mJ
t_{Eoff} =	0,14	μs

Figure 6 PFC MOSFET

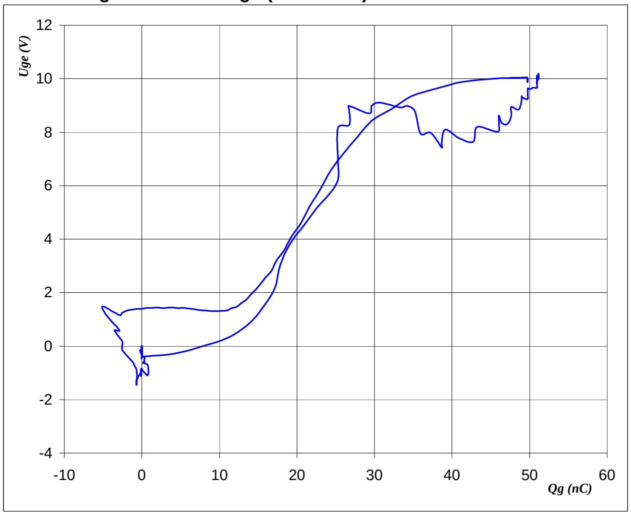
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	2,45	kW
E_{on} (100%) =	0,09	mJ
t_{Eon} =	0,0325	μs

Figure 7 PFC MOSFET

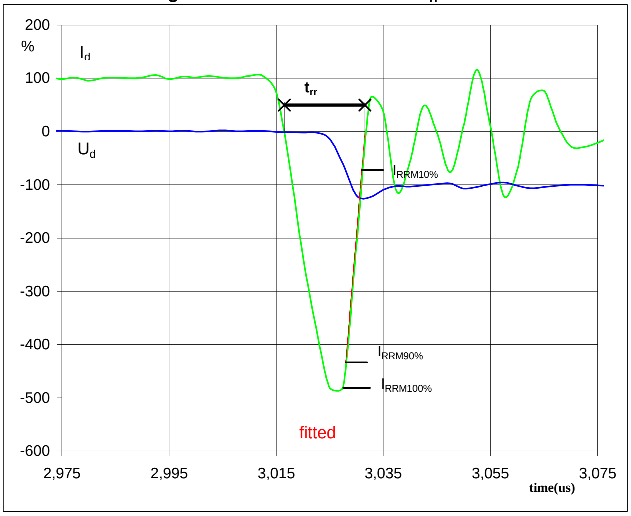
Gate voltage vs Gate charge (measured)



V_{GEoff} =	0	V
V_{GEon} =	10	V
V_C (100%) =	400	V
I_C (100%) =	6	A
Q_g =	51,14	nC

Figure 8 PFC FWD

Turn-off Switching Waveforms & definition of t_{rr}

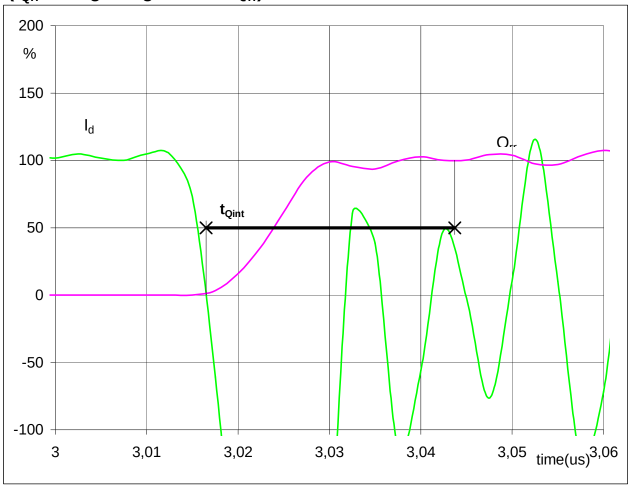


V_d (100%) =	400	V
I_d (100%) =	6	A
I_{RRM} (100%) =	-31	A
t_{rr} =	0,02	μs

Switching Definitions PFC

Figure 9 PFC FWD

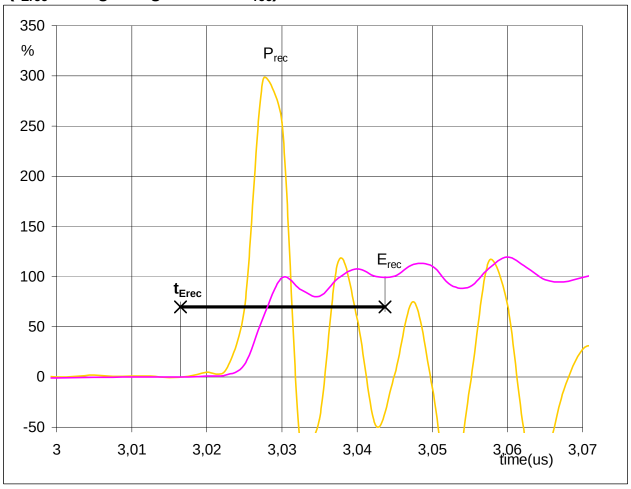
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr}= integrating time for Q_{rr})



I_d (100%) =	6	A
Q_{rr} (100%) =	0,29	µC
t_{Qint} =	0,03	µs

Figure 10 PFC FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	2,45	kW
E_{rec} (100%) =	0,04	mJ
t_{Erec} =	0,03	µs

Ordering Code and Marking - Outline - Pinout

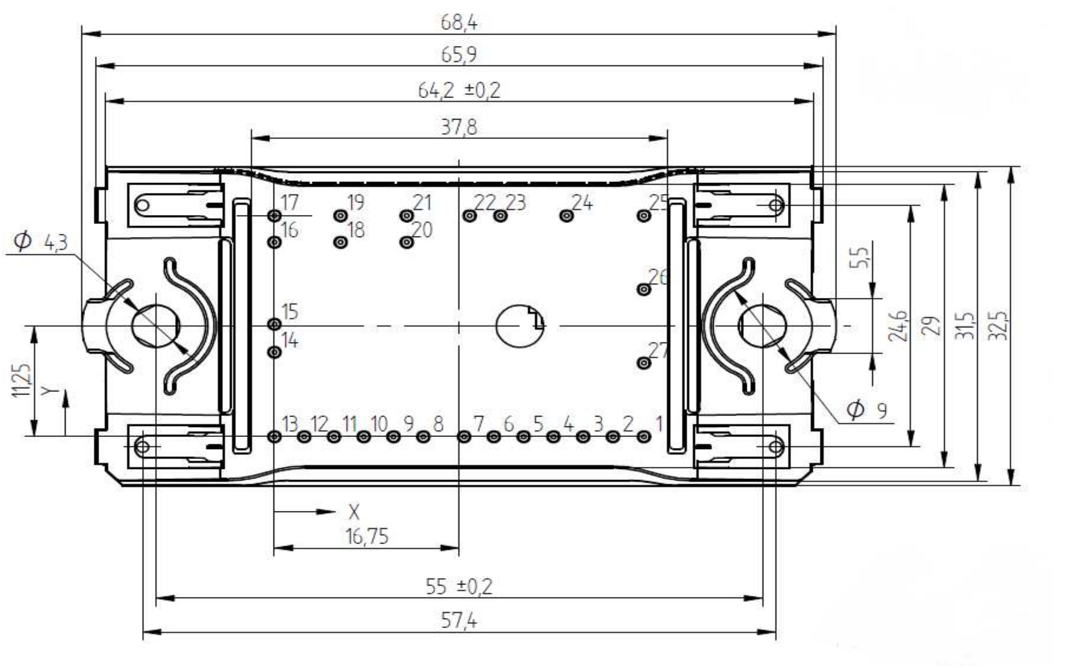
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
without thermal paste 17mm housing	10-F006PPA006SB-M682B	M682B	M682-B

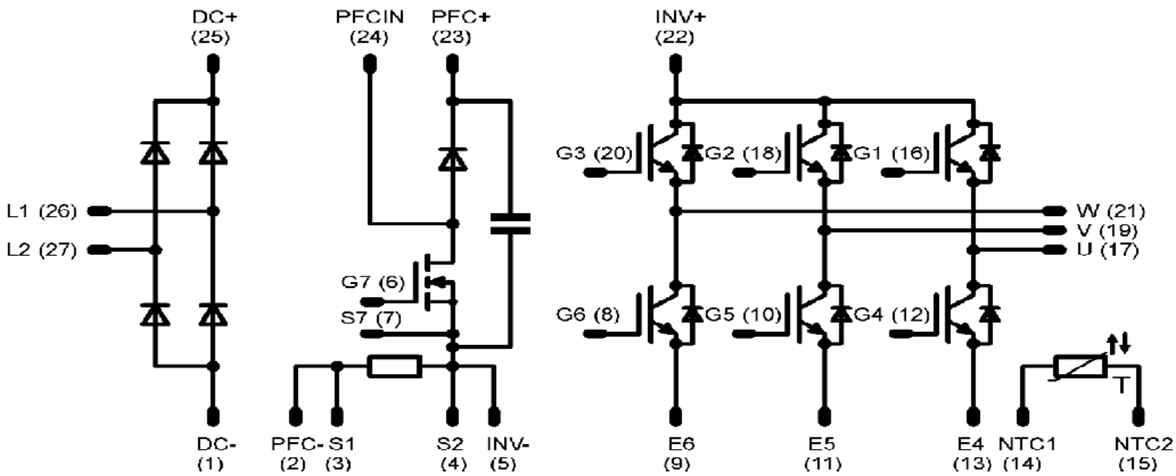
Outline

Pin table

Pin	X	Y
1	33,5	0
2	30,7	0
3	28	0
4	25,3	0
5	22,6	0
6	19,9	0
7	17,2	0
8	13,5	0
9	10,8	0
10	8,1	0
11	5,4	0
12	2,7	0
13	0	0
14	0	8,6
15	0	11,45
16	0	19,8
17	0	22,5
18	6	19,8
19	6	22,5
20	12	19,8
21	12	22,5
22	17,7	22,5
23	20,5	22,5
24	26,5	22,5
25	33,5	22,5
26	33,5	15
27	33,5	7,5



Pinout



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Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
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Final	Full Production	This datasheet contains final specifications. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.

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